

Chunsheng Jiang

List of Publications by Year in descending order

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docs citations

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1417
citing authors

#	ARTICLE	IF	CITATIONS
1	Steep-slope hysteresis-free negative capacitance MoS ₂ transistors. Nature Nanotechnology, 2018, 13, 24-28.	31.5	422
2	Steep-Slope WSe ₂ Negative Capacitance Field-Effect Transistor. Nano Letters, 2018, 18, 3682-3687.	9.1	97
3	MoS ₂ Negative Capacitance Field-Effect Transistors with Subthreshold Swing below the Physics Limit. Advanced Materials, 2018, 30, e1800932.	21.0	87
4	Thin, Transferred Layers of Silicon Dioxide and Silicon Nitride as Water and Ion Barriers for Implantable Flexible Electronic Systems. Advanced Electronic Materials, 2017, 3, 1700077.	5.1	61
5	Atomic threshold-switching enabled MoS ₂ transistors towards ultralow-power electronics. Nature Communications, 2020, 11, 6207.	12.8	52
6	A Closed Form Analytical Model of Back-Gated 2-D Semiconductor Negative Capacitance Field Effect Transistors. IEEE Journal of the Electron Devices Society, 2018, 6, 189-194.	2.1	35
7	Investigation of Negative Capacitance Gate-all-around Tunnel FETs Combining Numerical Simulation and Analytical Modeling. IEEE Nanotechnology Magazine, 2016, , 1-1.	2.0	28
8	Analytical drain current model for long-channel gate-all-around negative capacitance transistors with a metal-ferroelectric-insulator-semiconductor structure. Japanese Journal of Applied Physics, 2016, 55, 024201.	1.5	27
9	Negative Capacitance Oxide Thin-Film Transistor With Sub-60 mV/Decade Subthreshold Swing. IEEE Electron Device Letters, 2019, 40, 826-829.	3.9	26
10	Simulation-based study of negative capacitance double-gate junctionless transistors with ferroelectric gate dielectric. Solid-State Electronics, 2016, 126, 130-135.	1.4	25
11	Proton Conductor Gated Synaptic Transistor Based on Transparent IGZO for Realizing Electrical and UV Light Stimulus. IEEE Journal of the Electron Devices Society, 2019, 7, 38-45.	2.1	24
12	A carrier-based analytical theory for negative capacitance symmetric double-gate field effect transistors and its simulation verification. Journal Physics D: Applied Physics, 2015, 48, 365103.	2.8	22
13	Effects of parasitic capacitance on both static and dynamic electrical characteristics of back-gated two-dimensional semiconductor negative-capacitance field-effect transistors. Applied Physics Express, 2018, 11, 124101.	2.4	4
14	Investigation of the junctionless line tunnel field-effect transistor. , 2014, , .		2
15	A carrier-based analytic theory for electrical simulation of negative capacitance surrounding gate ferroelectric capacitor. , 2015, , .		1
16	An analytical charge-sheet drain current model for monolayer transition metal dichalcogenide negative capacitance field-effect transistors. , 2017, , .		1
17	Subthreshold Behaviors of Nanoscale Silicon and Germanium Junctionless Cylindrical Surrounding-Gate MOSFETs. ChemistrySelect, 2018, 3, .	1.5	1
18	Logic AND and OR realized in a single intelligent three dimension transistor. Applied Physics Express, 2019, 12, 104004.	2.4	1

#	ARTICLE	IF	CITATIONS
19	A rigorous analytical model for short-channel junctionless double-gate MOSFETs. , 2014, , .		0
20	Analytical drain current model for long-channel double-gate negative capacitance junctionless transistors using Landau theory. , 2016, , .		0